

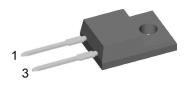
 V_{RRM} 600 V **FRED**

10 A 110 ns

Single Diode

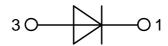
Part number

DFE10I600PM



Backside: Isolated

F1 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

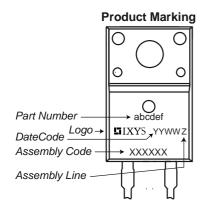
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Fast Diode					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			600	V	
V _{RRM}	max. repetitive reverse blocking ve	oltage	$T_{VJ} = 25^{\circ}C$			600	V	
IR	reverse current, drain current	$V_R = 600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			20	μΑ	
		$V_R = 480 \text{ V}$	$T_{VJ} = 125$ °C			1.5	mΑ	
V _F	forward voltage drop	I _F = 10 A	$T_{VJ} = 25^{\circ}C$			1.50	V	
		$I_F = 20 A$				1.77	V	
		I _F = 10 A	T _{VJ} = 150°C			1.38	V	
		$I_F = 20 A$				1.70	V	
I _{FAV}	average forward current	T _c =100°C	T _{VJ} = 150°C			10	Α	
		rectangular d = 0.5						
V _{F0}	threshold voltage		T _{VJ} = 150°C			0.98	V	
\mathbf{r}_{F}	slope resistance	oss calculation only				28.7	mΩ	
R _{thJC}	thermal resistance junction to case	е				4.2	K/W	
R _{thCH}	thermal resistance case to heatsin	nk			0.50		K/W	
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			30	W	
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			100	Α	
C	junction capacitance	$V_R = 400 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		5		pF	
I _{RM}	max. reverse recovery current	<u>, </u>	$T_{VJ} = 25 ^{\circ}\text{C}$		4		Α	
		$I_F = 10 \text{ A}; V_R = 300 \text{ V}$	$T_{VJ} = 125$ °C		2		Α	
t _{rr}	reverse recovery time	$\begin{cases} I_F = 10 \text{ A; } V_R = 300 \text{ V} \\ -di_F /dt = 100 \text{ A/} \mu \text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		110		ns	
)	$T_{VJ} = 125$ °C		25		ns	



Package TO-220FP					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					20	Α
T _{VJ}	virtual junction temperature				-55		150	°C
T _{op}	operation temperature				-55		125	°C
T _{stg}	storage temperature				-55		150	°C
Weight						2		g
M _D	mounting torque				0.4		0.6	Nm
F _c	mounting force with clip				20		60	N
d _{Spp/App}	croonago distanco on surfaco l stri	king distance through air	terminal to terminal	3.2	2.7			mm
$d_{Spb/Apb}$	creepage distance on surface striking distance through air		terminal to backside	2.5	2.5			mm
V	isolation voltage	t = 1 second	50/60 Hz, RMS; lisoL ≤ 1 mA		2500			V
		t = 1 minute			2100			V



Part description

D = Diode F = FRED

E = fast, low VF

10 = Current Rating [A]

I = Single Diode

600 = Reverse Voltage [V] PM = TO-220ACFP (2)

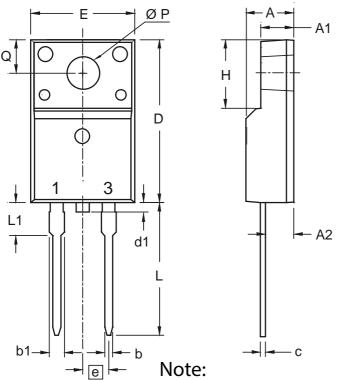
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DFE10I600PM	DFE10I600PM	Tube	50	503920

Similar Part	Package	Voltage class	
DSEI8-06A	TO-220AC (2)	600	
DSEI8-06AS	TO-263AB (D2Pak) (2)	600	

Equivalent Circuits for Simulation		* on die level	T _{VJ} = 150 °C	
$I \rightarrow V_0$	R_0	Fast Diode		
V _{0 max}	threshold voltage	0.98		V
$R_{0\;max}$	slope resistance *	25.7		$m\Omega$



Outlines TO-220FP



e e	note.
	All metal surface are
	matte pure tin plated
	except trimmed area.

Dim.	Millimeters		Inches		
DIIII.	min	max	min	max	
Α	4.50	4.90	0.177	0.193	
A1	2.34	2.74	0.092	0.108	
A2	2.56	2.96	0.101	0.117	
b	0.70	0.90	0.028	0.035	
b1	1.27	1.47	0.050	0.058	
С	0.45	0.60	0.018	0.024	
D	15.67	16.07	0.617	0.633	
d1	0	1.10	0	0.043	
Е	9.96	10.36	0.392	0.408	
е	2.54	BSC	0.100	BSC	
Н	6.48	6.88	0.255	0.271	
L	12.68	13.28	0.499	0.523	
L1	3.03	3.43	0.119	0.135	
ØΡ	3.08	3.28	0.121	0.129	
Q	3.20	3.40	0.126	0.134	





Fast Diode

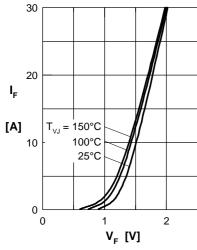


Fig. 1 Forward current I_F versus V_F

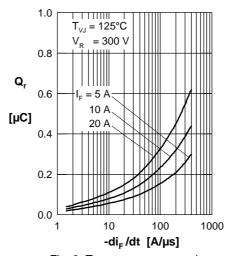


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

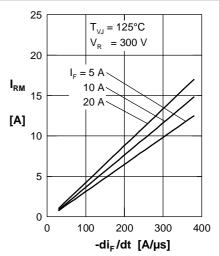


Fig. 3 Typ. peak reverse current I_{RM} versus -di_F/dt

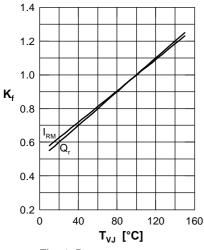


Fig. 4 Dyn. parameters $Q_{r, I_{RM}}$ versus T_{VJ}

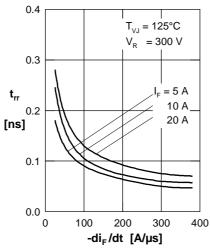


Fig. 5 Typ. recovery time t_{rr} versus -di_F/dt

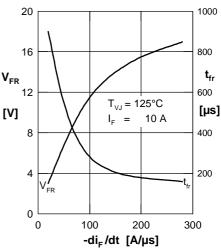


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

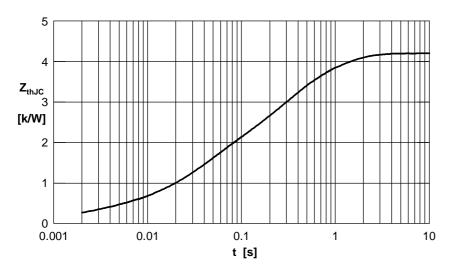


Fig. 7 Transient thermal impedance junction to case